

Centre for Energy Research

Seeking sustainable solutions for Africa



Nelson Mandela
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Effect of spectral changes on device and performance parameters of a mc-Si solar cell under spot illumination

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Outline

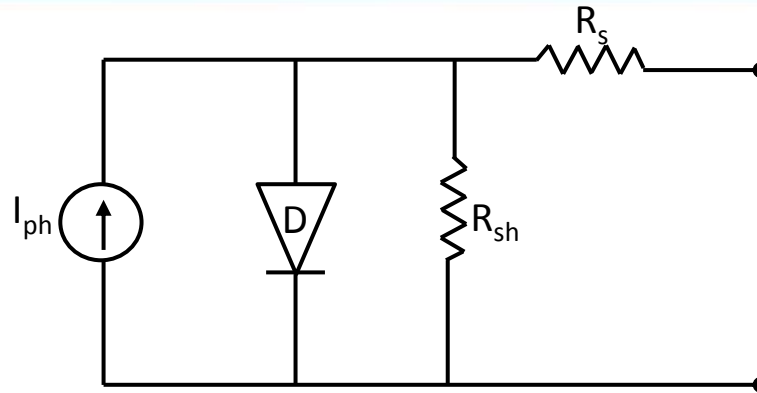
- Introduction
 - LBIC mapping technique
- Experimental set up
- Results
 - Photo-response mapping
 - Parameter extraction
- Conclusion
- Acknowledgement

- mc-Si contribute more than 50% of total Si for PV applications
- Produced mainly from low grade feedstock
 - ✓ High concentration of impurities and active defects
- Steady state I-V characteristics of p-n junction Si solar cell often described using equivalent circuit models
 - ✓ Single or double diode models



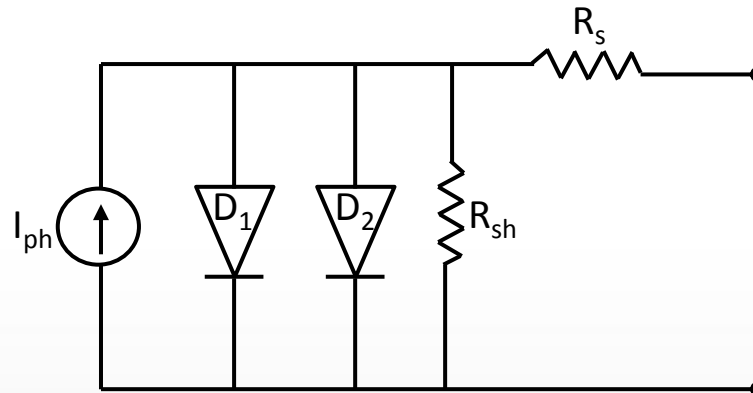
Introduction- Cell models

Single diode
model



$$I = I_{ph} - I_0 \left\{ \exp \left[q \left(\frac{V + IR_s}{nkT} \right) \right] - 1 \right\} - \frac{V + IR_s}{R_{sh}}$$

Double
diode model



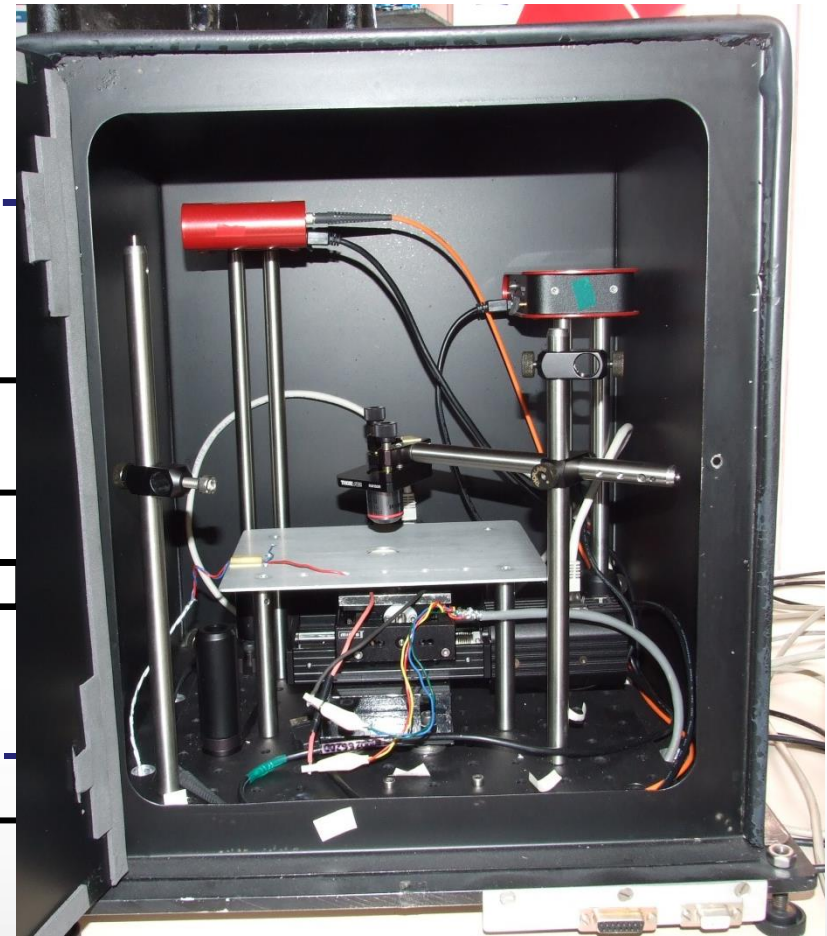
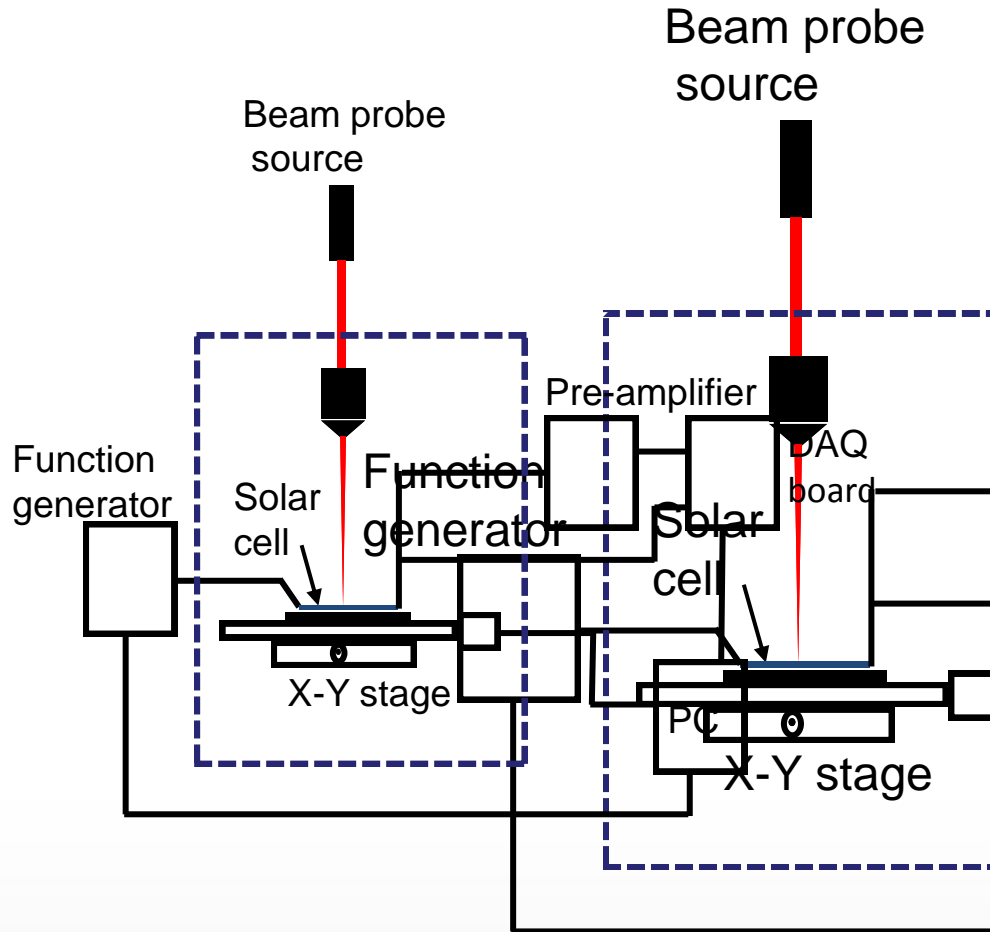
$$I = I_{ph} - I_{01} \left\{ \exp \left[q \left(\frac{V + IR_s}{n_1 kT} \right) \right] - 1 \right\} - I_{02} \left\{ \exp \left[q \left(\frac{V + IR_s}{n_2 kT} \right) \right] - 1 \right\} - \frac{V + IR_s}{R_{sh}}$$

- Device parameters control I-V characteristics
 - ✓ Determine performance of solar cell device
- PV characterisation involves extraction of I-V parameters
 - ✓ Device and performance parameters extracted at specific conditions
 - ✓ Under outdoor conditions, solar cells exposed to varying conditions
- Why PV characterisation?
 - ✓ Evaluation of performance
 - ✓ Quality control of devices

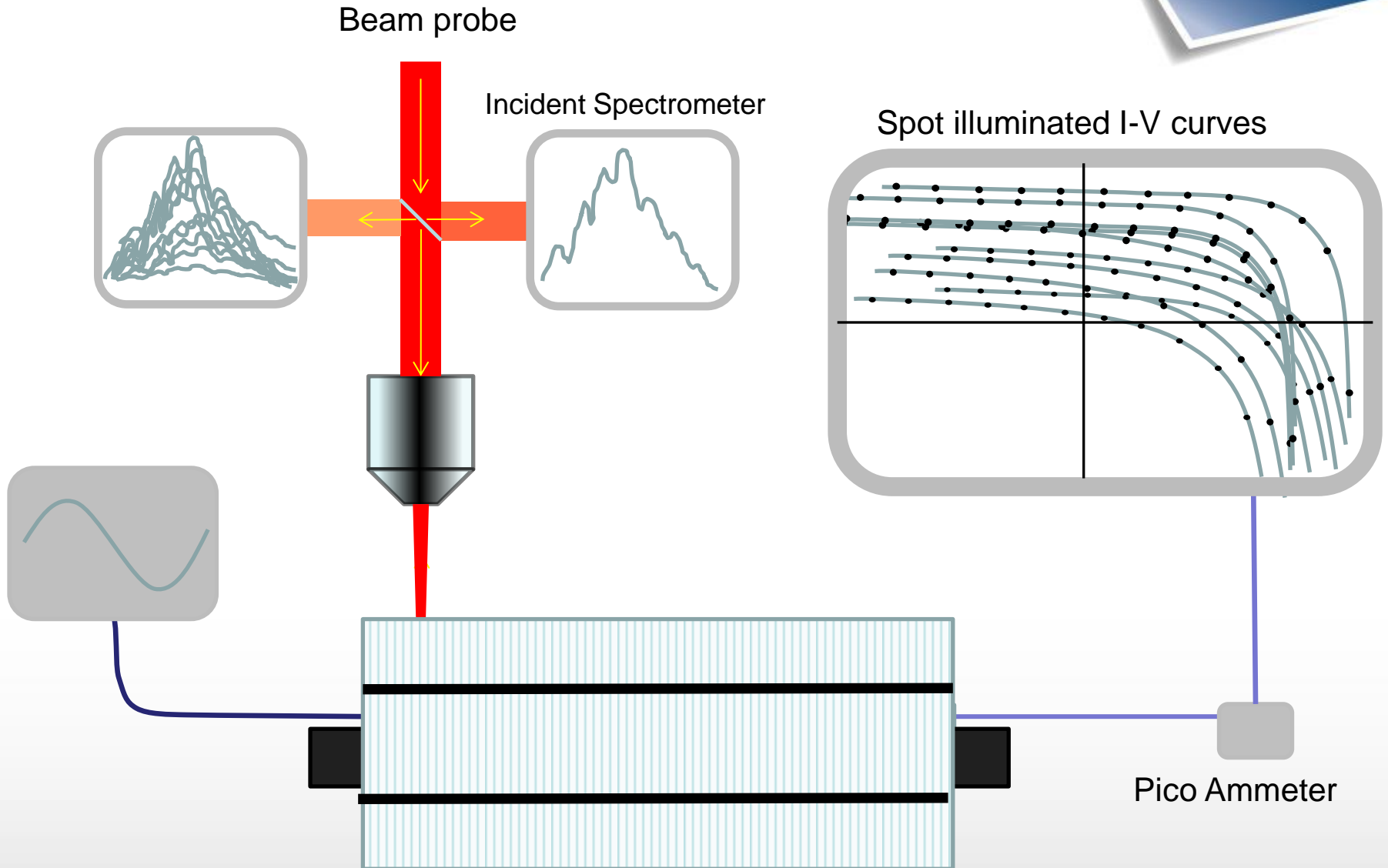
Introduction: LBIC

- Light beam Induced Current (LBIC)- a non destructive mapping technique
 - ✓ Beam scanned across cell surface in a raster pattern to generate localised current
- Photo-response mapping
 - ✓ Carrier generation uniformity
 - ✓ Presence and strength of current reducing features
- Carrier generation depth
 - ✓ Defect detection within device cross-section
- Point by point I-V curves
 - ✓ Parameter maps

Experimental set up



Data structure



Results: Photo-response mapping

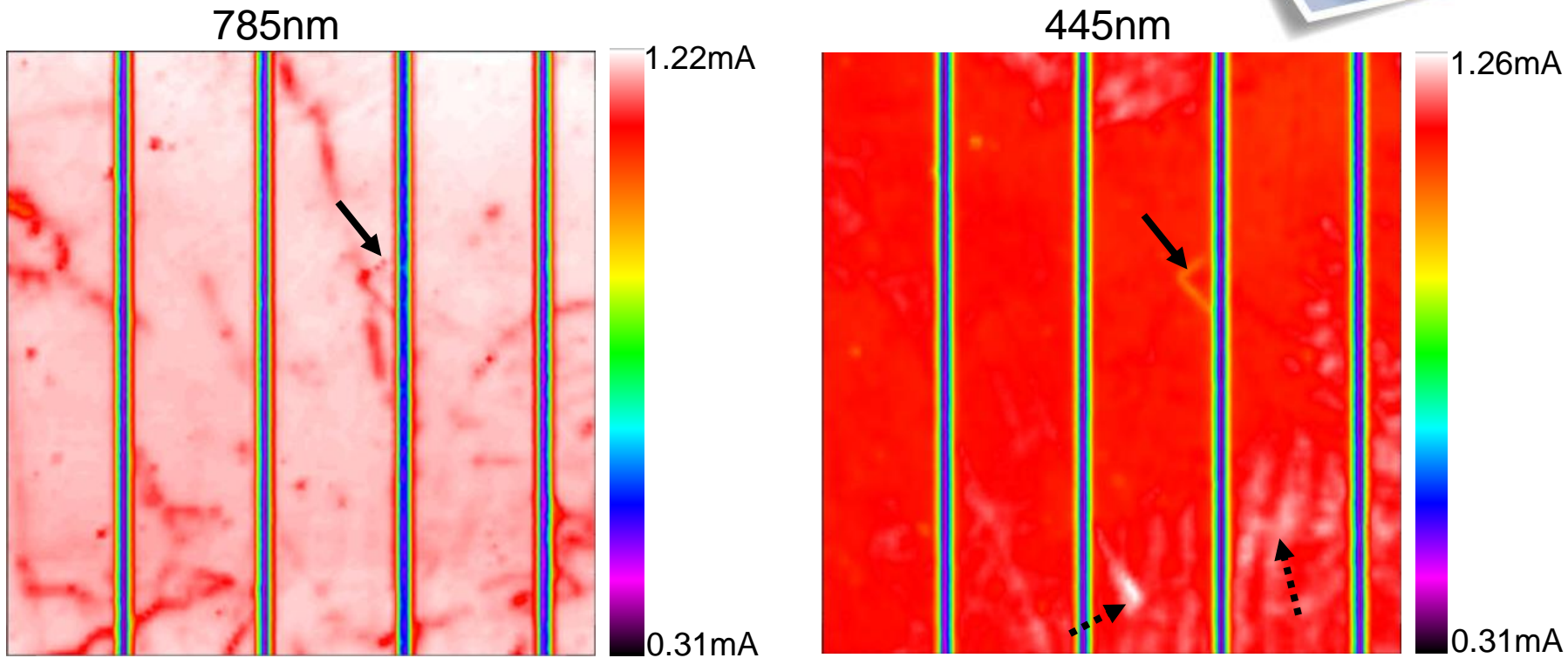
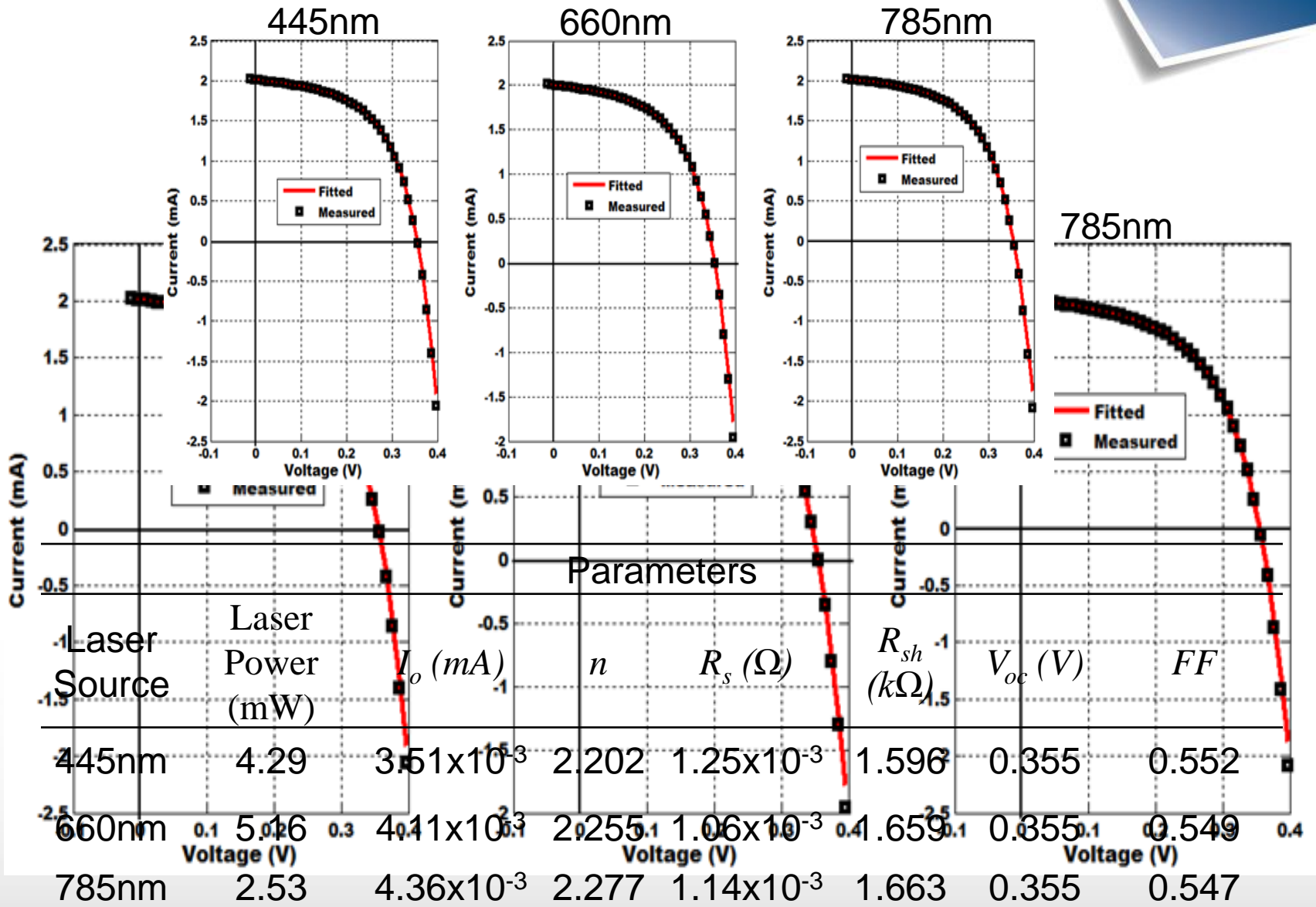


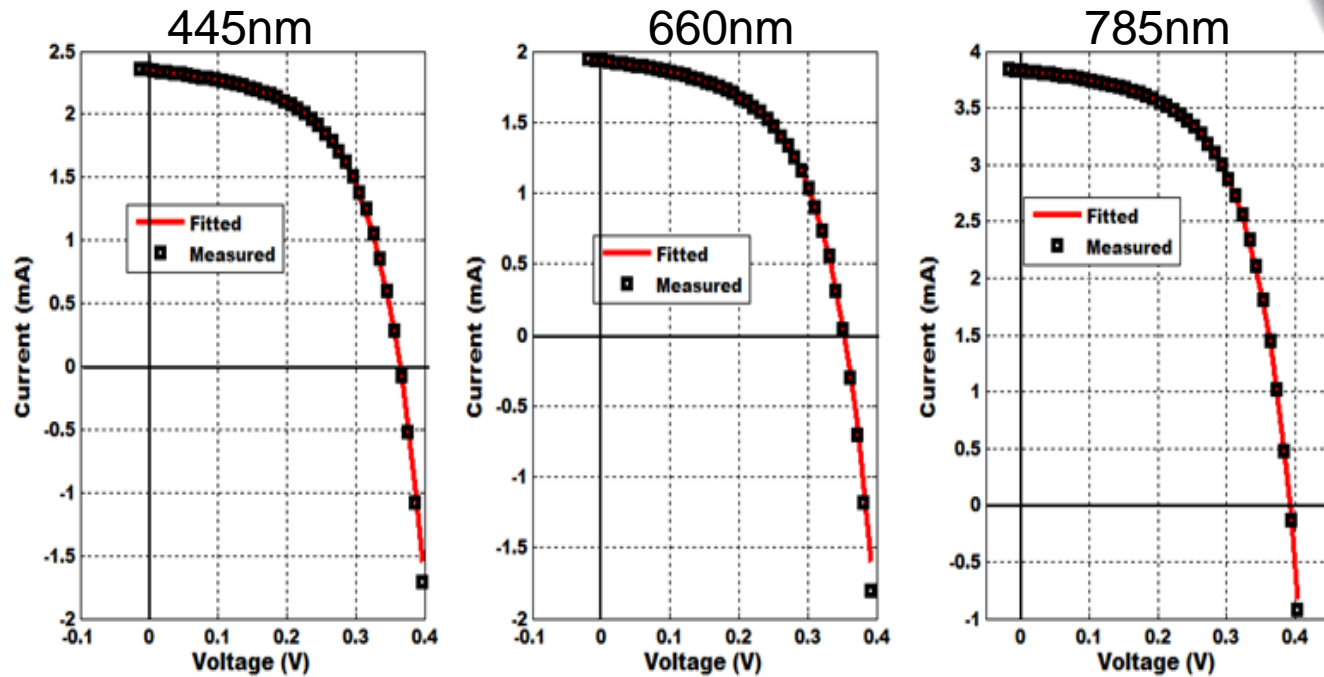
Photo-response depends on wavelength

- ✓ Due to differences in absorption coefficient

Effect of spectral change



Spectral change- cont'd

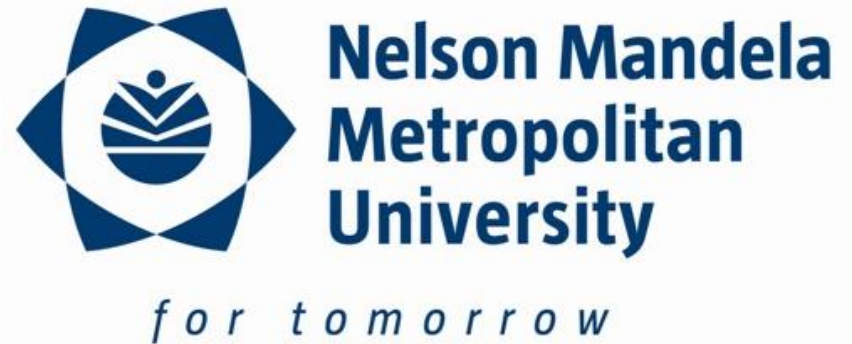


Parameters

Laser Source	n	I_o (mA)	R_{sh} (k Ω)	R_s (Ω)	I_{sc} (mA)	V_{oc} (V)	FF
445nm	2.309	4.84×10^{-3}	1.683	9.50×10^{-4}	2.35	0.364	0.554
660nm	2.302	4.62×10^{-3}	1.694	1.35×10^{-3}	1.93	0.353	0.544
785nm	2.217	3.90×10^{-3}	1.584	4.36×10^{-3}	3.82	0.392	0.588

- Photo-response mapping of mc-Si
 - ✓ Photo-response maps obtained at two spectral conditions
 - ✓ Current reducing defects identified
- Parameter extraction carried out at different spectral conditions
 - ✓ Point I-V parameters extracted
 - ✓ Variation in extracted point I-V parameters observed
 - Changing recombination mechanisms

Acknowledgement



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Makerere University



Thank you

